

Description

Features

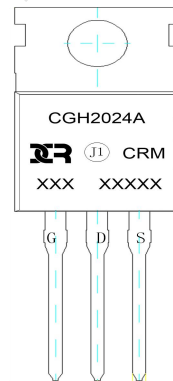
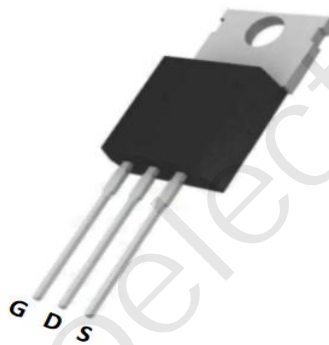
- 200V, 60A
 $R_{DS(ON)}$ Typ = 22mΩ @ $V_{GS} = 10V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	TUBE(pcs)	Reel (pcs)	Per Carton (pcs)
CRMCGH2024A	CRMCGH2024A	TO-220C-3L	TUBE	50	1000	5000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	200	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	60
		$T_C = 100^\circ\text{C}$	36
I_{DM}	Pulsed Drain Current ⁽¹⁾	240	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	605	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	176
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.71	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	200	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.5	3.1	3.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 30A	-	22	28.6	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	1293	-	pF
C _{oss}	Output Capacitance		-	1890	-	pF
C _{rss}	Reverse Transfer Capacitance		-	50	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 100V, I _D = 30A	-	45	-	nC
Q _{gs}	Gate Source Charge		-	15	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	13	-	nC

Switching Characteristics

t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 100V I _D = 30A, R _{GEN} = 3Ω	-	28	-	ns
t _r	Turn-On Rise Time		-	23	-	ns
t _{d(off)}	Turn-Off DelayTime		-	35	-	ns
t _f	Turn-Off Fall Time		-	24	-	ns

Drain-Source Diode Characteristics and Max Ratings

I _S	Maximum Continuous Drain to Source Diode Forward Current	V _{GS} = 0V, I _S = 30A	-	-	60	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	240	A
V _{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time		-	120	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	400	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=30V, V_G=10V, R_G=25ohm, L=10mH, I_{AS}=11A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

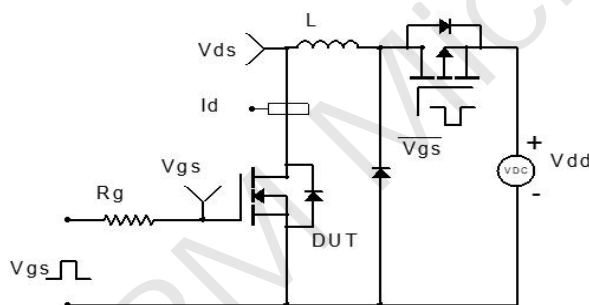


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

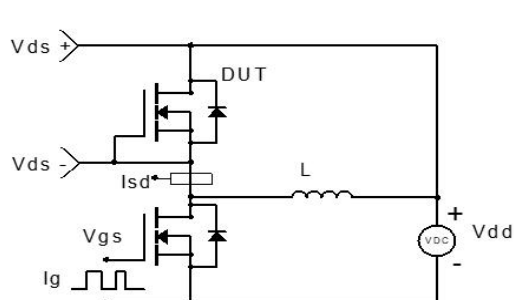
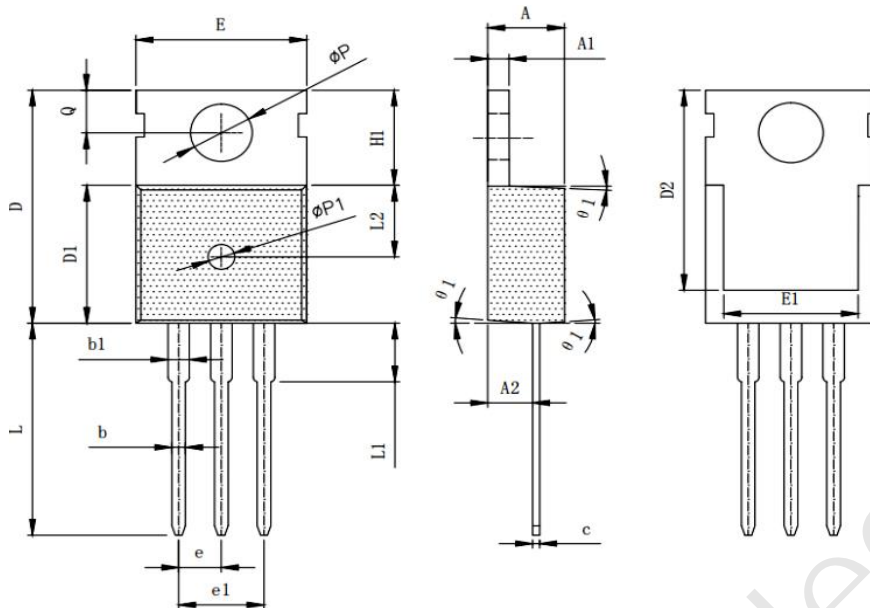


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220C-3L)



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.25	1.30	1.35
A2	2.30	2.40	2.50
b	0.70	0.80	0.90
b1	1.25	1.35	1.45
c	0.40	0.50	0.60
D	15.50	15.80	16.10
D1	9.10	9.20	9.30
D2	12.73	12.83	12.93
E	9.70	9.90	10.20
E1	7.60	8.00	8.40
e	2.54 (BSC)		
e1	5.08 (BSC)		
HI	6.30	6.50	6.80
L	12.75	13.08	13.50
L1	--	--	3.10
L2	4.30	4.60	4.90
ϕP	3.50	3.60	3.70
ϕP1	1.40	1.50	1.60
Q	2.70	--	2.90
θ 1	2°	4°	6°

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